

## SIPMOS® Power Transistor

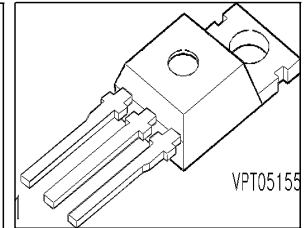
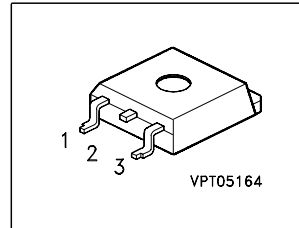
## BUZ 111S

### Features

- N channel
- Enhancement mode
- Avalanche rated
- dv/dt rated
- 175 °C operating temperature

### Product Summary

Drain source voltage	$V_{DS}$	55	V
Drain-Source on-state resistance	$R_{DS(on)}$	0.008	$\Omega$
Continuous drain current	$I_D$	80	A



Type	Package	Ordering Code	Packaging
BUZ111S	P-TO220-3-1	Q67040-S4003-A2	Tube
BUZ111S E3045A	P-TO263-3-2	Q67040-S4003-A6	Tape and Reel
BUZ111S E3045	P-TO263-3-2	Q67040-S4003-A5	Tube

Pin 1	Pin 2	Pin 3
G	D	S

### Maximum Ratings, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ °C}$ , <sup>1)</sup> $T_C = 100\text{ °C}$	$I_D$	80 80	A
Pulsed drain current $T_C = 25\text{ °C}$	$I_{Dpulse}$	320	
Avalanche energy, single pulse $I_D = 80\text{ A}$ , $V_{DD} = 25\text{ V}$ , $R_{GS} = 25\text{ }\Omega$	$E_{AS}$	700	mJ
Avalanche energy, periodic limited by $T_{jmax}$	$E_{AR}$	30	
Reverse diode dv/dt $I_S = 80\text{ A}$ , $V_{DS} = 40\text{ V}$ , $di/dt = 200\text{ A}/\mu\text{s}$ , $T_{jmax} = 175\text{ °C}$	dv/dt	6	kV/ $\mu\text{s}$
Gate source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation $T_C = 25\text{ °C}$	$P_{tot}$	300	W
Operating and storage temperature	$T_j, T_{stg}$	-55... +175	°C
IEC climatic category; DIN IEC 68-1		55/175/56	

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Characteristics</b>					
Thermal resistance, junction - case	$R_{thJC}$	-	-	0.5	K/W
Thermal resistance, junction - ambient, leded	$R_{thJA}$	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm <sup>2</sup> cooling area <sup>2)</sup>	$R_{thJA}$	-	-	62 40	

**Electrical Characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Static Characteristics</b>					
Drain- source breakdown voltage $V_{GS} = 0\text{ V}$ , $I_D = 0.25\text{ mA}$	$V_{(BR)DSS}$	55	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 240\text{ }\mu\text{A}$	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current $V_{DS} = 50\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_j = 25\text{ }^\circ\text{C}$ $V_{DS} = 50\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$	$I_{DSS}$	-	0.1	1 100	$\mu\text{A}$
Gate-source leakage current $V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$	$I_{GSS}$	-	10	100	nA
Drain-Source on-state resistance $V_{GS} = 10\text{ V}$ , $I_D = 80\text{ A}$	$R_{DS(on)}$	-	0.0065	0.008	$\Omega$

<sup>1</sup>current limited by bond wire

<sup>2</sup> Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical without blown air.

**Electrical Characteristics**, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Dynamic Characteristics</b>					
Transconductance $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 80\text{ A}$	$g_{fs}$	30	73	-	S
Input capacitance $V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$	$C_{iss}$	-	3600	4500	pF
Output capacitance $V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$	$C_{oss}$	-	1100	1375	
Reverse transfer capacitance $V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$	$C_{rss}$	-	550	690	
Turn-on delay time $V_{DD} = 30\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 80\text{ A}$ , $R_G = 2.4\text{ }\Omega$	$t_{d(on)}$	-	25	37	ns
Rise time $V_{DD} = 30\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 80\text{ A}$ , $R_G = 2.4\text{ }\Omega$	$t_r$	-	30	45	
Turn-off delay time $V_{DD} = 30\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 80\text{ A}$ , $R_G = 2.4\text{ }\Omega$	$t_{d(off)}$	-	65	95	
Fall time $V_{DD} = 30\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 80\text{ A}$ , $R_G = 2.4\text{ }\Omega$	$t_f$	-	40	60	

**Electrical Characteristics**, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

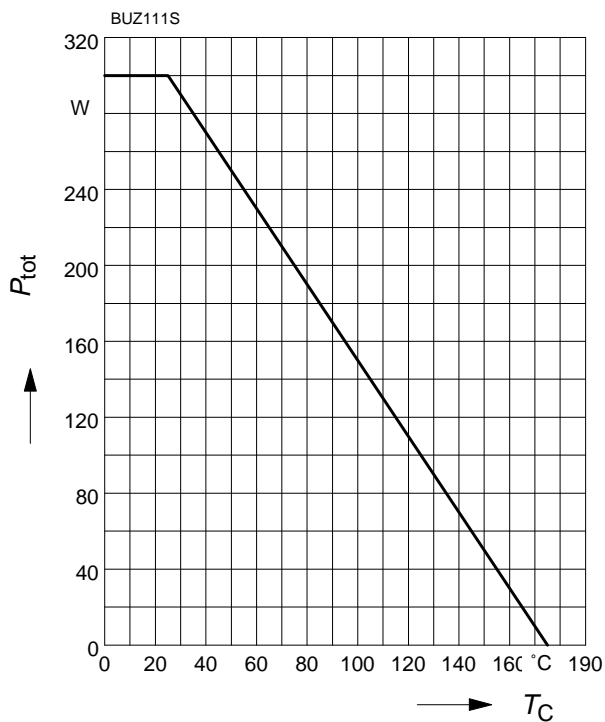
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Dynamic Characteristics</b>					
Gate to source charge $V_{DD} = 40\text{ V}, I_D = 80\text{ A}$	$Q_{gs}$	-	18	27	nC
Gate to drain charge $V_{DD} = 40\text{ V}, I_D = 80\text{ A}$	$Q_{gd}$	-	61	91.5	
Gate charge total $V_{DD} = 40\text{ V}, I_D = 80\text{ A}, V_{GS} = 0\text{ to }10\text{ V}$	$Q_g$	-	125	185	
Gate plateau voltage $V_{DD} = 40\text{ V}, I_D = 80\text{ A}$	$V_{(\text{plateau})}$	-	5.45	-	V

**Reverse Diode**

Inverse diode continuous forward current $T_C = 25\text{ }^\circ\text{C}$	$I_S$	-	-	80	A
Inverse diode direct current, pulsed $T_C = 25\text{ }^\circ\text{C}$	$I_{SM}$	-	-	320	
Inverse diode forward voltage $V_{GS} = 0\text{ V}, I_F = 160\text{ A}$	$V_{SD}$	-	1.25	1.8	V
Reverse recovery time $V_R = 30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$	$t_{rr}$	-	105	160	ns
Reverse recovery charge $V_R = 30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$	$Q_{rr}$	-	0.29	0.45	$\mu\text{C}$

**Power Dissipation**

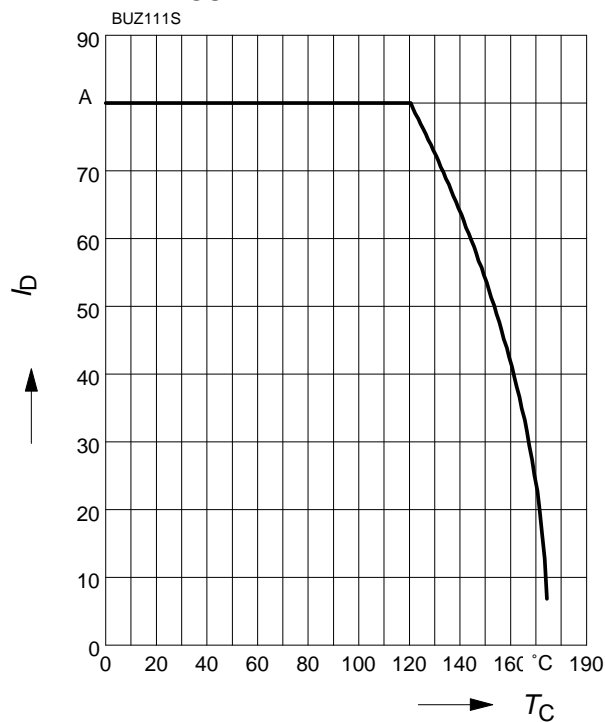
$P_{tot} = f(T_C)$



**Drain current**

$I_D = f(T_C)$

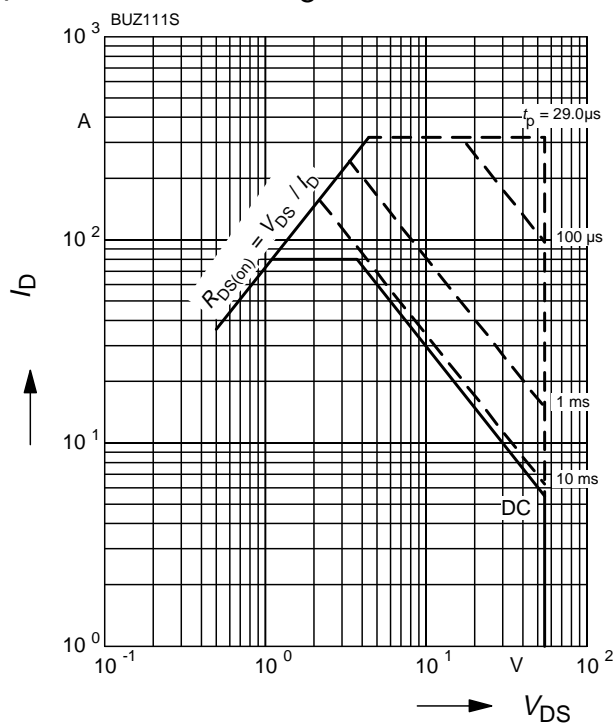
parameter:  $V_{GS} \geq 10\text{ V}$



**Safe operating area**

$I_D = f(V_{DS})$

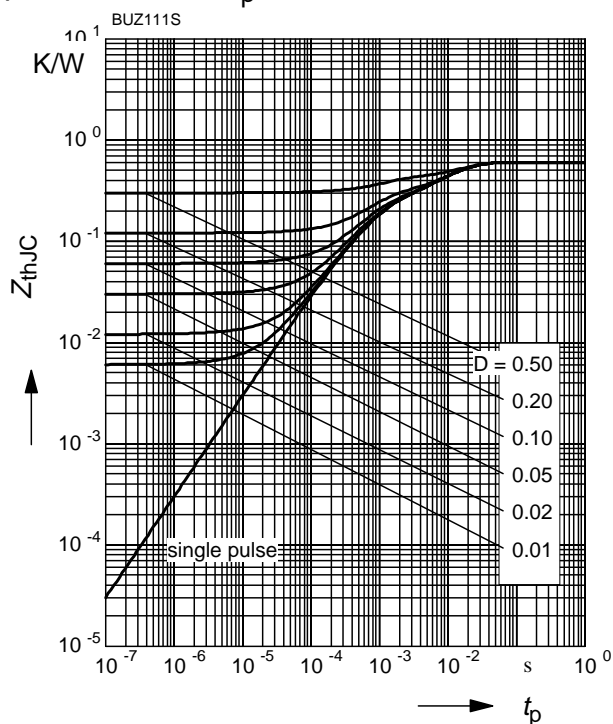
parameter :  $D = 0, T_C = 25\text{ °C}$



**Transient thermal impedance**

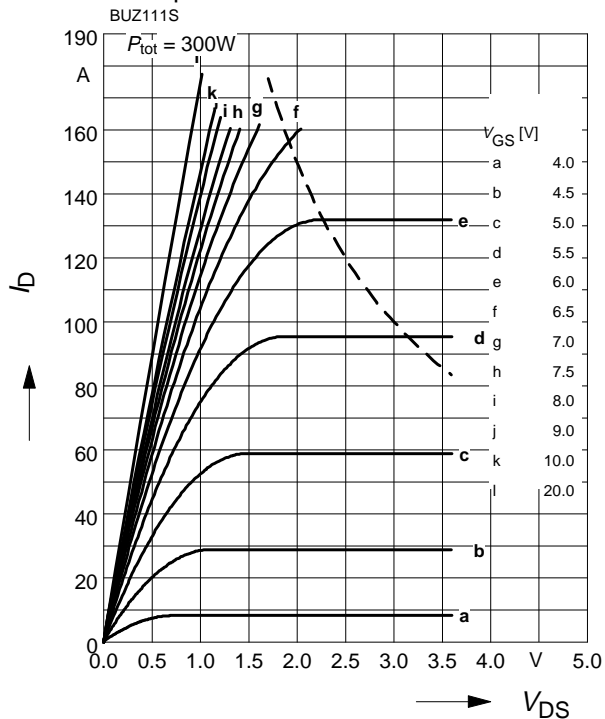
$Z_{thJC} = f(t_p)$

parameter :  $D = t_p/T$



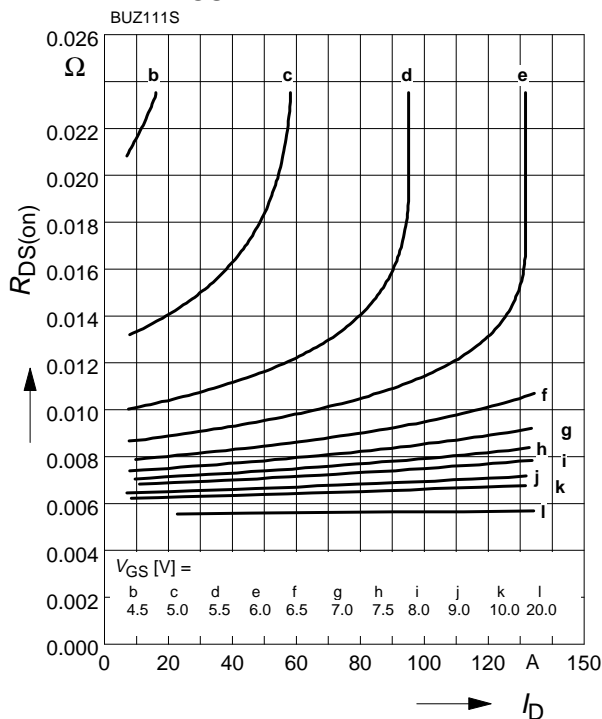
**Typ. output characteristics**

$I_D = f(V_{DS})$   
parameter:  $t_p = 80 \mu s$



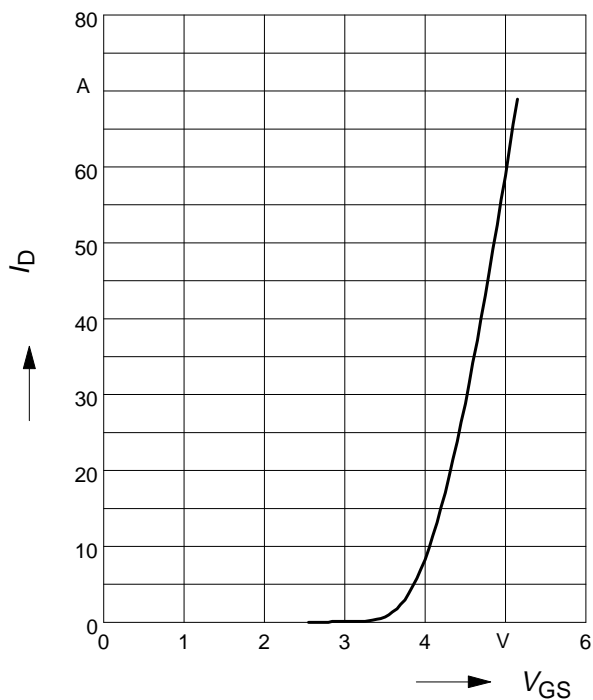
**Typ. drain-source-on-resistance**

$R_{DS(on)} = f(I_D)$   
parameter:  $V_{GS}$



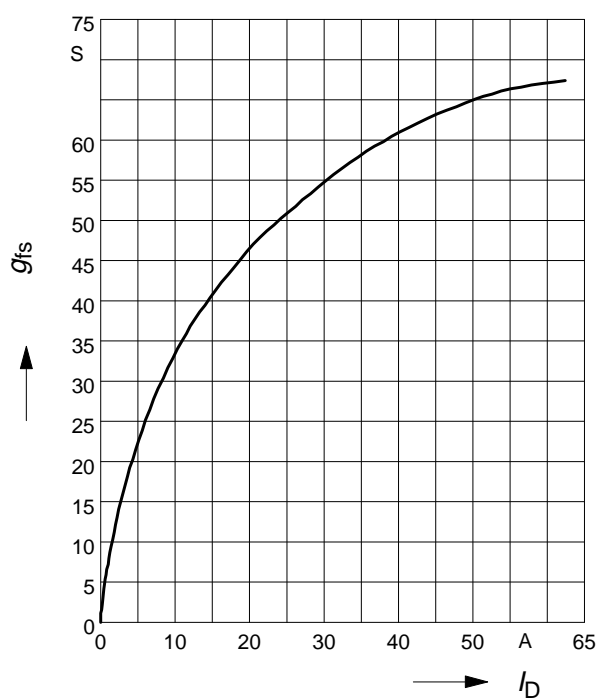
**Typ. transfer characteristics  $I_D = f(V_{GS})$**

parameter:  $t_p = 80 \mu s$   
 $V_{DS} \geq 2 \times I_D \times R_{DS(on)} \max$



**Typ. forward transconductance**

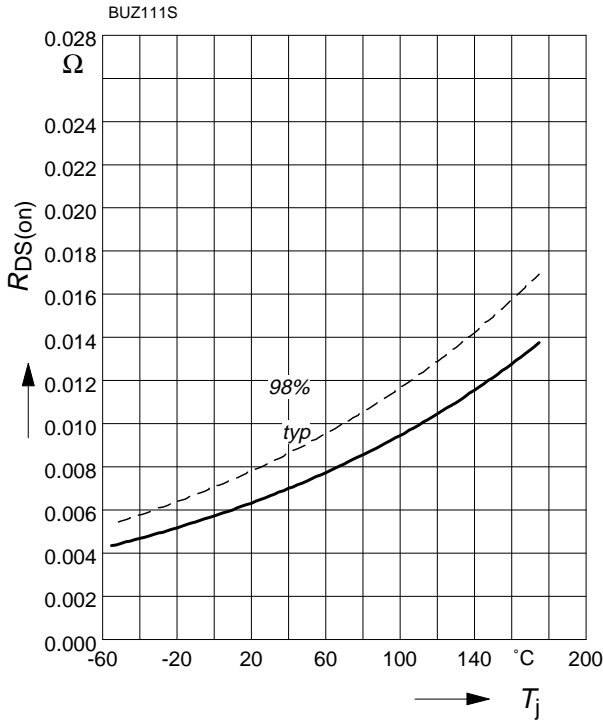
$g_{fs} = f(I_D); T_j = 25^\circ C$   
parameter:  $g_{fs}$



**Drain-source on-resistance**

$$R_{DS(on)} = f(T_j)$$

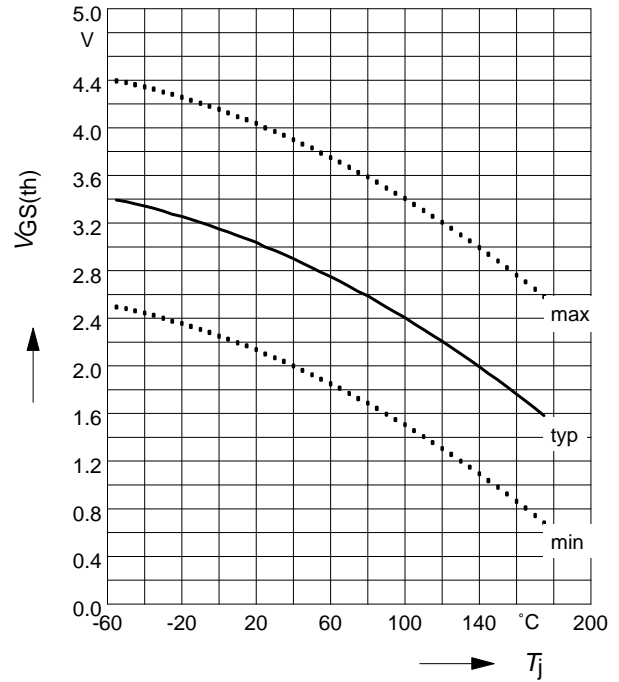
parameter :  $I_D = 80 \text{ A}$ ,  $V_{GS} = 10 \text{ V}$



**Gate threshold voltage**

$$V_{GS(th)} = f(T_j)$$

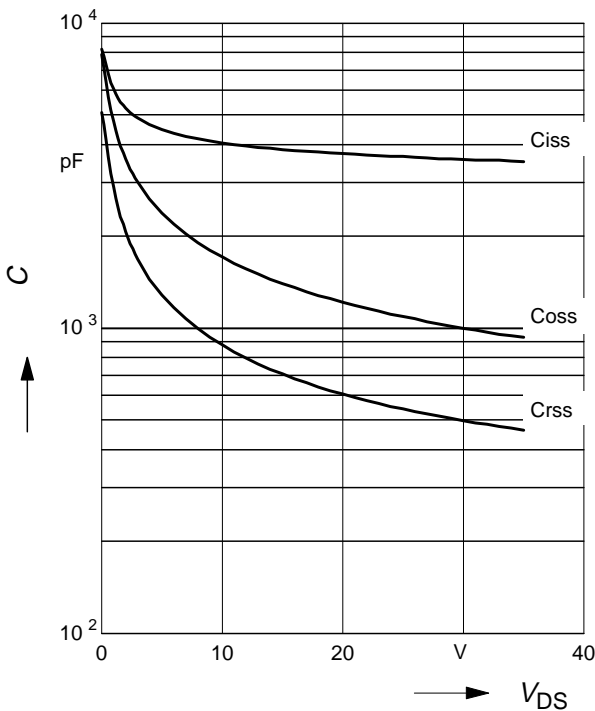
parameter :  $V_{GS} = V_{DS}$ ,  $I_D = 240 \mu\text{A}$



**Typ. capacitances**

$$C = f(V_{DS})$$

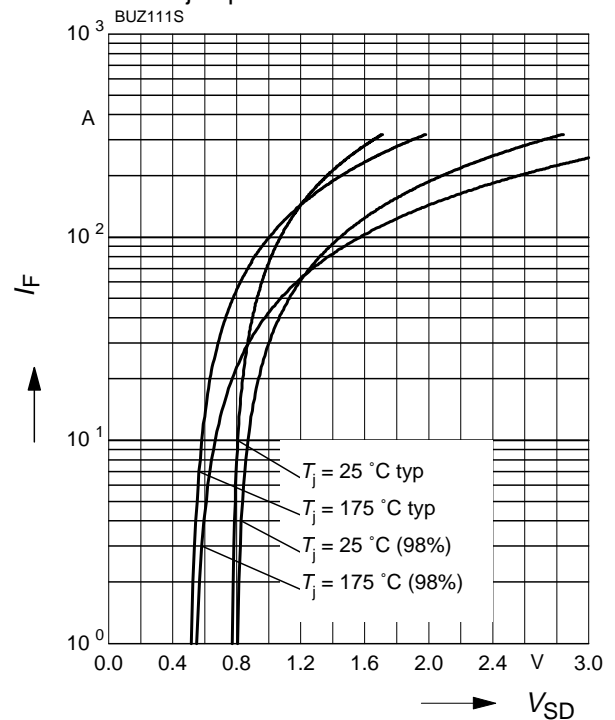
parameter:  $V_{GS} = 0 \text{ V}$ ,  $f = 1 \text{ MHz}$



**Forward characteristics of reverse diode**

$$I_F = f(V_{SD})$$

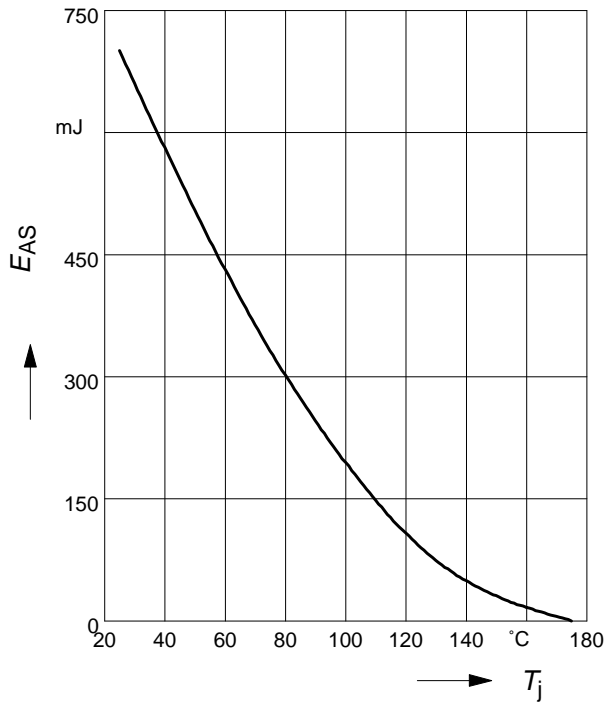
parameter:  $T_j$ ,  $t_p = 80 \mu\text{s}$



**Avalanche Energy  $E_{AS} = f(T_j)$**

parameter:  $I_D = 80\text{ A}$ ,  $V_{DD} = 25\text{ V}$

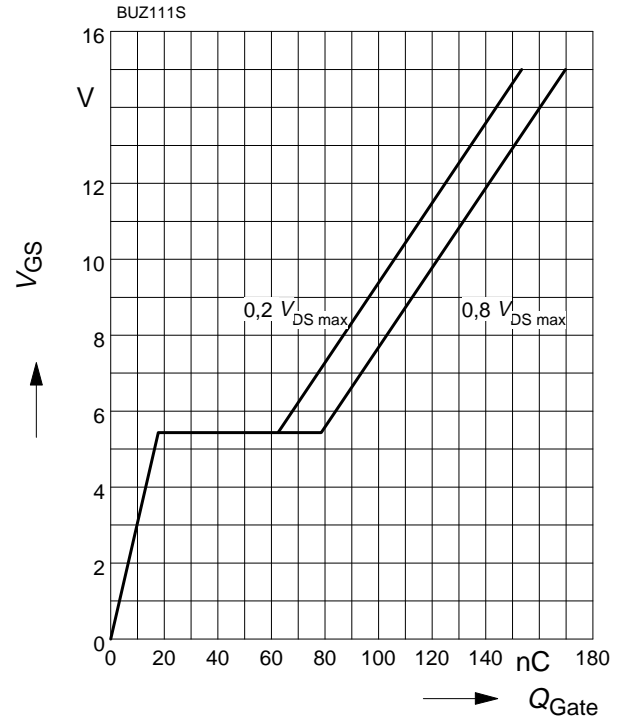
$R_{GS} = 25\ \Omega$



**Typ. gate charge  $V_{GS} = f(Q_{Gate})$**

parameter:  $I_{D\ puls} = 80\text{ A}$

parameter:  $I_{D\ puls} = 80\text{ A}$



**Drain-source breakdown voltage  $V_{(BR)DSS} = f(T_j)$**

parameter:  $V_{GS} = 0\text{ V}$ ,  $I_D = 0\text{ A}$

